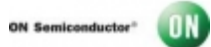
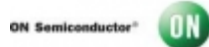
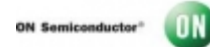


specificazioni	
Modello di prodotti	FQA48N20
fabbricante	Fairchild/ON Semiconductor
Descrizione	MOSFET N-CH 200V 48A TO-3P
Categoria	Prodotti a semiconduttore discreti > Transistor-FET ,
Stato parte	5764 pcs Stock
Vgs (th) (max) a Id	5V @ 250μA
Tecnologia	MOSFET (Metal Oxide)
Contenitore dispositivo fornitore	TO-3P
Serie	QFET®
Rds On (max) a Id, Vgs	50 mOhm @ 24A, 10V
Dissipazione di potenza (max)	280W (Tc)
imballaggio	Tube
Contenitore / involucro	TO-3P-3, SC-65-3
temperatura di esercizio	-55°C ~ 150°C (TJ)
Tipo montaggio	Through Hole
Capacità di ingresso (Ciss) (Max) @ Vds	5000pF @ 25V
Carica Gate (Qg) (Max) @ Vgs	130nC @ 10V
Tipo FET	N-Channel
Caratteristica FET	-
Tensione drain-source (Vdss)	200V
Corrente - Drain continuo (Id) @ 25 ° C	48A (Tc)

 FQA48N20 AMI Semiconductor / ON Semiconductor MOSFET N-CH 200V 48A TO-3P	 FQA55N10 AMI Semiconductor / ON Semiconductor MOSFET N-CH 100V 61A TO-3P	 FQA55N25 Fairchild/ON Semiconductor MOSFET N-CH 250V 55A TO-3P	 FQA55N25 AMI Semiconductor / ON Semiconductor MOSFET N-CH 250V 55A TO-3P
 FQA46P06 FSC FQA46P06 FSC	 FQA47P06 Fairchild/ON Semiconductor MOSFET P-CH 60V 55A TO-3PN	 FQA55N10 Fairchild/ON Semiconductor MOSFET N-CH 100V 61A TO-3P	 FQA50N06 FAIRCHI FAIRCHI TO-220

Di Più

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